

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	"20030062561".pn. and (partially adj pinned adj photodiode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 07:53
L2	0	(semiconductor adj image adj sensor) and ((sio2 or (silicon adj dioxide)) near (sin or (silicon adj nitride)) near (thickness or thick))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 08:14
L3	0	(semiconductor adj image adj sensor) and ((sio2 or (silicon adj dioxide) or "sio.sub.2") near (sin or (silicon adj nitride)) near (thickness or thick))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 08:14
L4	0	(semiconductor adj image adj sensor) and ((sio2 or (silicon adj dioxide) or "sio.sub.2") near (sin or (silicon adj nitride) or "si.sub.3n.sub.4") near (thickness or thick))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 08:15
L5	5	(semiconductor adj image adj sensor) and ((sio2 or (silicon adj dioxide) or "sio.sub.2") with (sin or (silicon adj nitride) or "si.sub.3n.sub.4") with (thickness or thick))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 08:18
L6	9	(semiconductor adj image adj sensor) and ((sio2 or (silicon adj dioxide) or "sio.sub.2") same (sin or (silicon adj nitride) or "si.sub.3n.sub.4") same (thickness or thick))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 08:20
L7	24	(semiconductor adj image adj sensor) and ((sio2 or (silicon adj dioxide) or "sio.sub.2") and (sin or (silicon adj nitride) or "si.sub.3n.sub.4") and (thickness or thick))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 08:31
L8	2	"20010022371".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 08:31

S1	0	(semiconductor adj image adj sensor) and pixel and (photosensing adj portion) and silicide and prevention and thickness and (anti adj reflective) and wavelength	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 08:13
S2	0	(semiconductor adj image adj sensor) and pixel and (photosensing) and silicide and prevention and thickness and (anti adj reflective) and wavelength	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/30 17:16
S3	0	(semiconductor adj image adj sensor) and pixel and (photosensor) and silicide and prevention and thickness and (anti adj reflective) and wavelength	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/30 17:16
S4	0	(semiconductor adj image adj sensor) and pixel and silicide and prevention and thickness and (anti adj reflective) and wavelength	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/30 17:17
S5	1	(semiconductor adj image adj sensor) and pixel and silicide and thickness and (anti adj reflective) and wavelength	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/30 17:17
S6	1	(semiconductor adj image adj sensor) and pixel and silicide and (anti adj reflective) and wavelength	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/30 17:18
S7	2	(semiconductor adj image adj sensor) and pixel and silicide and (anti adj reflective)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/30 17:19
S8	26	(semiconductor adj image adj sensor) and pixel and silicide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/30 17:42

S9	4	(semiconductor adj image adj sensor) and pixel and silicide and photosensor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/30 17:19
S10	18	(image adj sensor) and pixel and silicide and (arc or (anti adj reflective adj coating)) and photosensor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/30 17:47
S11	171	(cmos adj image adj sensor) and (arc or (anti adj reflective adj coating))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 07:49
S12	150	(cmos adj image adj sensor) and (arc or (antireflective adj coating))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 10:20
S13	22	(image adj sensor) and (arc or (antireflective adj coating)) and cmos and locos and well	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 07:41
S14	13	(image adj sensor) and (arc or (antireflective adj coating)) and active and photosensing	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 07:42
S15	88	(image adj sensor) and (arc or (antireflective adj coating)) and active and photosensor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 07:44
S16	5	(image adj sensor) and (arc or (antireflective adj coating)) and (transistor adj (area or portion or region)) and (sensor adj (area or portion or region))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 07:46

S17	5	(arc or (antireflective adj coating)) and (transistor adj (area or portion or region)) and (sensor adj (area or portion or region))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 07:47
S18	31	(arc or (antireflective adj coating)) and (active adj (area or portion or region)) and (sensor adj (area or portion or region))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 07:47
S19	4629	(cmos adj image adj sensor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 09:58
S20	1034	257/53.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 09:59
S21	1097	257/82.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 10:00
S22	235	257/113.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 10:04
S23	649	257/21.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 10:04
S24	774	257/184.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 10:08

S25	561	257/290.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 10:10
S26	1493	257/431.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 10:11
S27	1499	257/432.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 10:11
S28	355	257/437.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 10:13
S29	1323	257/461.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 10:14
S30	524	257/462.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 10:14
S31	249	257/464.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 10:16
S32	2	silicide near (anti adj reflective)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 10:18

S33	9	silicide near (antireflective)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 10:17
S34	203	silicide with (anti adj reflective)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 10:18
S35	413	silicide same (anti adj reflective)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 10:19
S36	94	silicide with (antireflective)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 10:30
S37	204	silicide same (antireflective)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 10:19
S38	35	(cmos adj image adj sensor) and (arl or antireflective)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 10:21
S39	65	(cmos adj image adj sensor) and (arl or (anti adj reflective))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 10:21
S40	479	silicide with (prevent adj formation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 10:31

S41	212	silicide near (prevent adj formation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 10:34
S42	4	(silicide near (prevent adj formation)) same (arc or antireflective or (anti adj reflective))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 10:51
S43	11	(silicide with (prevent adj formation)) same (arc or antireflective or (anti adj reflective))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 10:54
S44	13	(silicide same (prevent adj formation)) same (arc or antireflective or (anti adj reflective))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 11:31
S45	316	438/69.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 11:31
S46	293	438/72.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 11:34
S47	399	438/636.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 14:39
S48	2	"4724323".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 15:17

S49	2	"20020109157".pn. and wavelength	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 15:53
S50	0	"20020109157".pn. and pinned	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 15:53
S51	0	"6906364".pn. and pinned	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 15:53
S52	17	partially adj pinned adj photodiode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 07:53